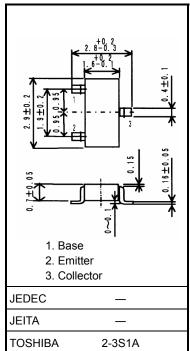
TOSHIBA Transistor Silicon NPN Epitaxial Type (Darlington Power)

2SD2719

- Solenoid Drive Applications
- \bigcirc Motor Drive Applications
- High DC current gain: h_{FE} = 2000 (min) (V_{CE} = 2 V, I_C = 1 A)
- Zener diode included between collector and base

Absolute Maximum Ratings (Ta = 25°C)

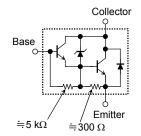
Characteristic		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	50	V	
Collector-emitter voltage		V _{CEO}	60±10	V	
Emitter-base voltage		V _{EBO}	8	V	
Collector current	DC	Ι _C	0.8	A	
	Pulse	I _{CP}	3		
Base current		Ι _Β	0.5	А	
Collector power dissipation	DC	P _C (Note)	0.8	W	
	t = 10 s	FC (NOIG)	1.25		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	–55 to 150	°C	



- Note1: Mounted on an FR4 board (glass-epoxy; 1.6 mm thick; Cu area, 645 mm^2)
- Weight: 0.01 g (typ.)
- Note2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

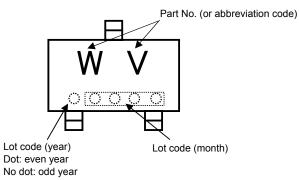
Equivalent Circuit



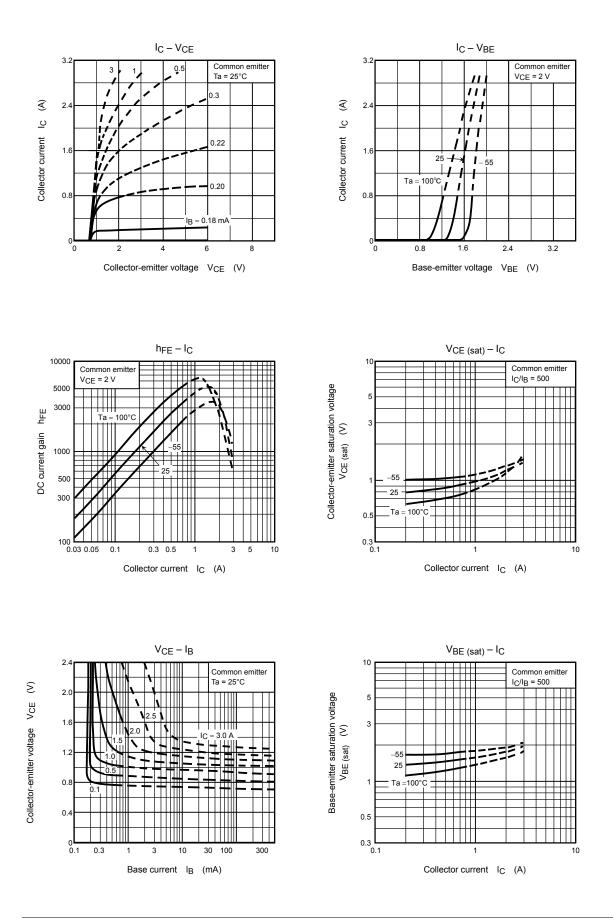
Electrical Characteristics (Ta = 25°C)

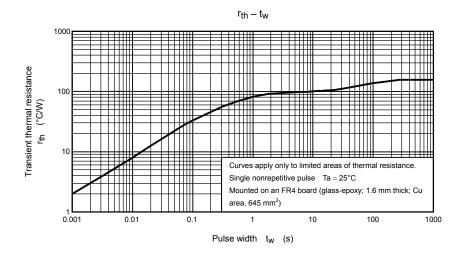
Characteristic		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current		I _{CBO}	$V_{CB}=45~V,~I_{E}=0$	_	_	10	μA
		ICEO	$V_{CE}=45~V,~I_{E}=0$	_	_	10	μA
Emitter cutoff current		I _{EBO}	$V_{EB} = 8 V, I_{C} = 0$	0.80	_	4.0	mA
Collector-emitter breakdown voltage		V (BR) CEO	$I_{C} = 10 \text{ mA}, I_{B} = 0$	50	60	70	V
DC current gain		h _{FE}	$V_{CE} = 2 V, I_C = 1 A$	2000		_	
Collector-emitter saturation voltage		V _{CE (sat) (1)}	$I_{C} = 0.5 \text{ A}, I_{B} = 1 \text{ mA}$	_	_	1.2	V
		V _{CE (sat) (2)}	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$	_	_	1.5	V
Base-emitter saturation voltage		V _{BE (sat)}	$I_C = 1 \text{ A}, I_B = 1 \text{ mA}$	_	_	2.0	V
Switching time	Turn-on time	t _{on}	Input 20 μ s 5V \downarrow		0.4		
	Storage time	t _{stg}		_	4.0	_	μS
	Fall time	t _f			0.6		

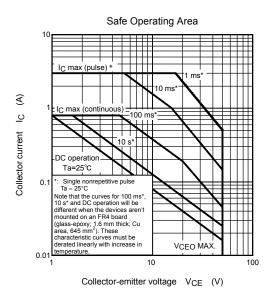
Marking



TOSHIBA







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20070701-EN

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